

PHPT60606PY

60 V, 6 A PNP high power bipolar transistor

9 December 2014

Product data sheet

1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT60606NY.

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-60	V
I _C	collector current		-	-	-6	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; pulsed	-	-	-12	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -6 A; I_B = -600 mA; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	-	66	88	mΩ



60 V, 6 A PNP high power bipolar transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	Е	emitter		в—
3	Е	emitter	[q]	1%
4	В	base	وققق	sym132
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PHPT60606PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT60606PY	0606PAB

60 V, 6 A PNP high power bipolar transistor

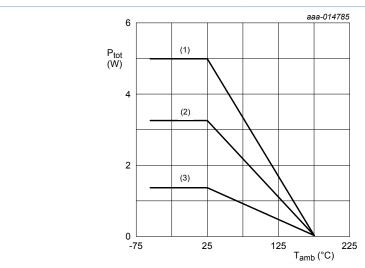
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-60	V
V _{CEO}	collector-emitter voltage	open base		-	-60	V
V _{EBO}	emitter-base voltage	open collector		-	-8	V
I _C	collector current			-	-6	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; pulsed		-	-12	Α
I _B	base current			-	-800	mA
I _{BM}	peak base current	t _p ≤ 1 ms; pulsed		-	-1.2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.35	W
			<u>[2]</u>	-	3.25	W
			[<u>3]</u>	-	5	W
			<u>[4]</u>	-	25	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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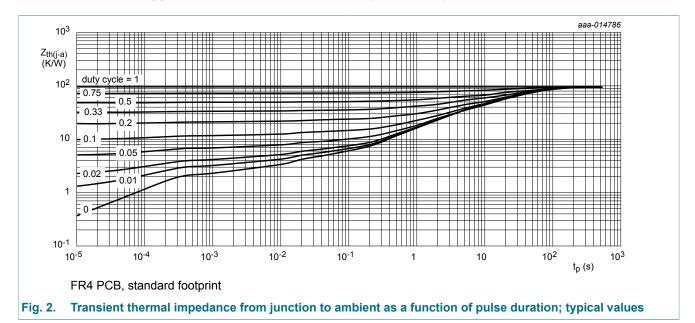
60 V, 6 A PNP high power bipolar transistor

9. Thermal characteristics

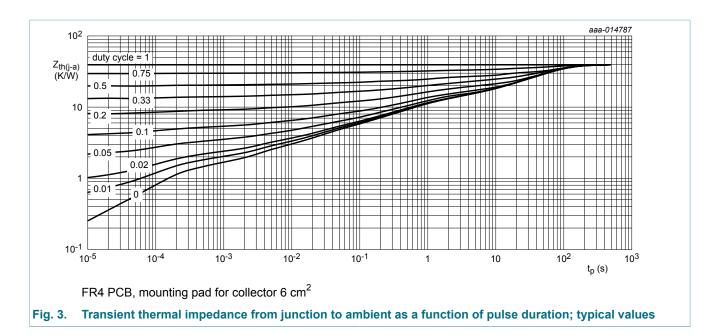
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	-	111	K/W
		[2]	-	-	46	K/W	
	ambient		[3]	-	-	30	K/W
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



60 V, 6 A PNP high power bipolar transistor



10. Characteristics

Table 7. Characteristics

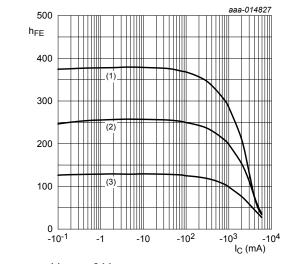
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -48 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -48 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = -48 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -8 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -500 mA; T_{amb} = 25 °C	120	200	-	
		V_{CE} = -2 V; I_{C} = -1 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	110	180	-	
		V_{CE} = -2 V; I_{C} = -3 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	60	100	-	
		V_{CE} = -2 V; I_{C} = -6 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	20	30	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -1 A; I_{B} = -50 mA; t_{p} ≤ 300 µs; δ ≤ 0.02; T_{amb} = 25 °C	-	-75	-110	mV
		I_C = -3 A; I_B = -300 mA; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	-	-155	-230	mV
		I_{C} = -6 A; I_{B} = -600 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-395	-525	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -6 A; I_{B} = -600 mA; pulsed; $t_{p} \le 300 \mu\text{s}; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	66	88	mΩ

PHPT60606PY

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60 V, 6 A PNP high power bipolar transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{BEsat} base-emitter satur voltage	base-emitter saturation voltage	I_C = -1 A; I_B = -50 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-0.85	-0.95	V
		I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02; T_{amb}$ = 25 °C	-	-1	-1.1	V
		I_{C} = -6 A; I_{B} = -600 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-1.1	-1.3	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -0.5 A; T_{amb} = 25 °C	-	-0.75	-0.85	V
t _d	delay time	V_{CC} = -12.5 V; I_{C} = -3 A; I_{Bon} = -150 mA; I_{Boff} = 150 mA; T_{amb} = 25 °C	-	15	-	ns
t _r	rise time		-	110	-	ns
t _{on}	turn-on time		-	125	-	ns
ts	storage time		-	185	-	ns
t _f	fall time		-	70	-	ns
t _{off}	turn-off time		-	255	-	ns
f _T	transition frequency	V _{CE} = -10 V; I _C = -500 mA; f = 100 MHz; T _{amb} = 25 °C	-	110	-	MHz
C _c	collector capacitance	V_{CB} = -10 V; I_E = 0 A; i_e = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	57	-	pF



 $V_{CE} = -2 V$

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 4. DC current gain as a function of collector current; typical values

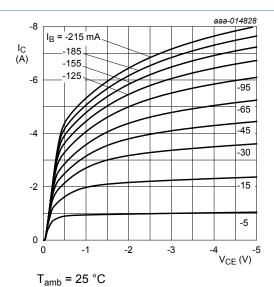
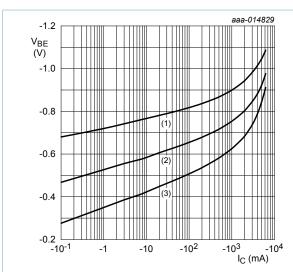


Fig. 5. Collector current as a function of collectoremitter voltage; typical values

60 V, 6 A PNP high power bipolar transistor



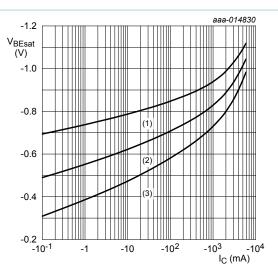
$$V_{CE} = -2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb}$$
 = 100 °C

Fig. 6. Base-emitter voltage as a function of collector current; typical values



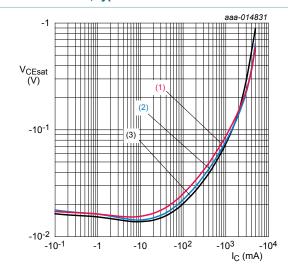
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



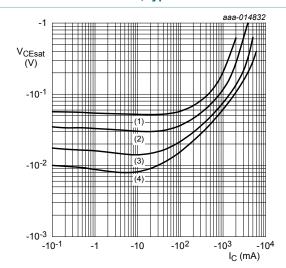
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



(1)
$$I_C/I_B = 100$$

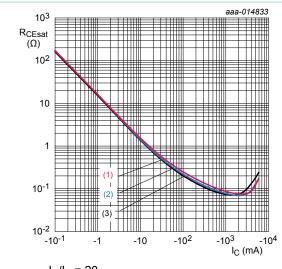
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 20$$

$$(4) I_{C}/I_{B} = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

60 V, 6 A PNP high power bipolar transistor



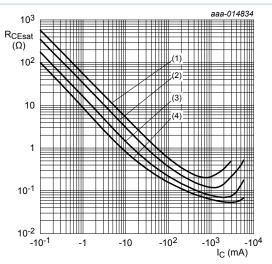
 $I_C/I_B = 20$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



 T_{amb} = 25 °C

(1) $I_C/I_B = 100$

(2) $I_C/I_B = 50$

(3) $I_C/I_B = 20$

(4) $I_{\rm C}/I_{\rm B} = 10$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

60 V, 6 A PNP high power bipolar transistor

11. Test information

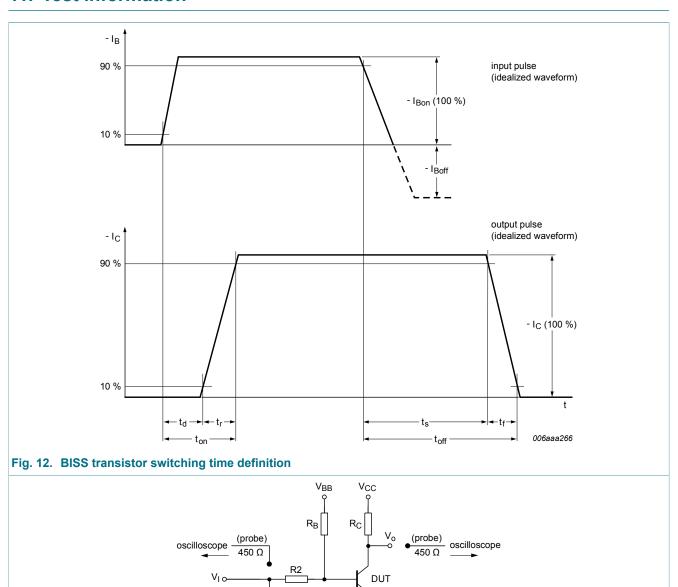


Fig. 13. Test circuit for switching times

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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60 V, 6 A PNP high power bipolar transistor

12. Package outline

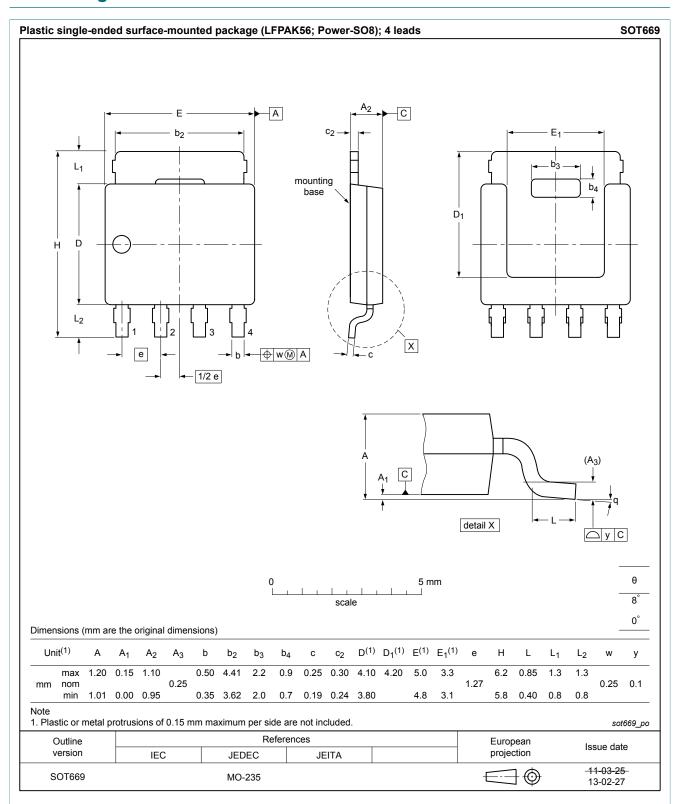
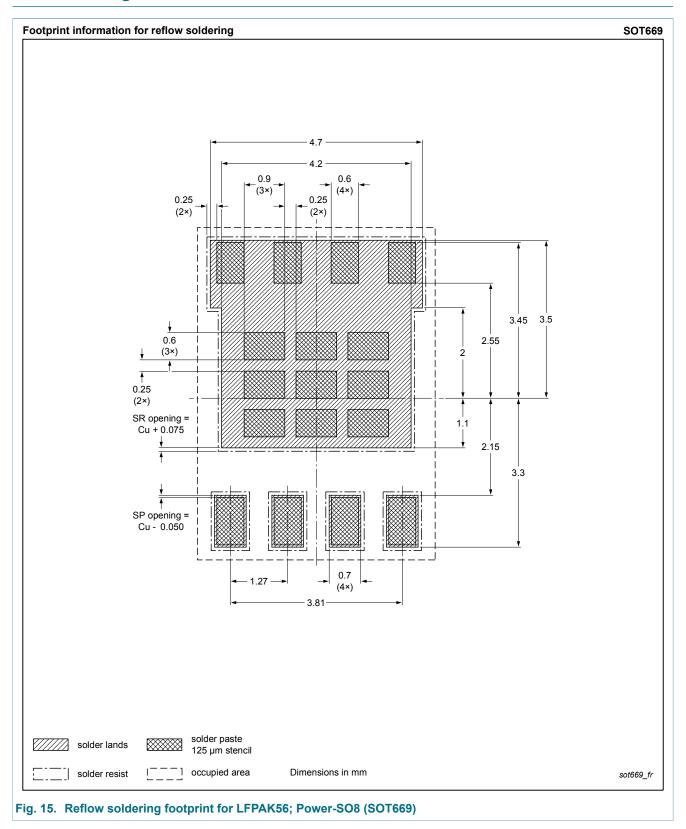


Fig. 14. Package outline LFPAK56; Power-SO8 (SOT669)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT60606PY v.1	20141209	Product data sheet	-	-

60 V, 6 A PNP high power bipolar transistor

15. Legal information

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60 V, 6 A PNP high power bipolar transistor

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60 V, 6 A PNP high power bipolar transistor

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	5
11	Test information	9
11.1	Quality information	9
12	Package outline	10
13	Soldering	11
14	Revision history	12
15	Legal information	13
15.1	Data sheet status	13
15.2	Definitions	13
15.3	Disclaimers	13
15.4	Trademarks	14

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